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Profile and material characterization of sine-like surface relief Ni gratings by spectroscopic ellipsometry



J.Mistrík^{1*}, R. Antoš², M. Karlovec¹, K. Pálka¹, Mir. Vlček¹, Mil. Vlček³

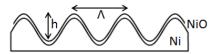
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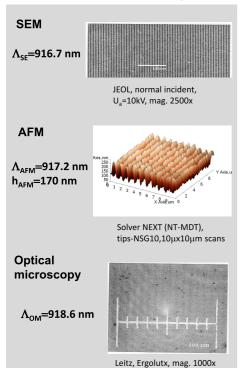
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A. Motivation

Spectroscopic ellipsometry (SE) performed in a wide spectral range is capable of monitoring various profile and material properties of periodically patterned nanostructures with high sensitivity, such as the period, width, depth and shape of patterned elements, native oxide overlayers, or the edge roughness of the patterned grooves [1]. We apply it to investigate the geometric properties of sinusoidally modulated surface-relief gratings, which are of high interest for many optical devices but has received almost no attention by SE. By comparing SE spectra with simulations with varied geometrical parameters, we can determine both the relief shape and the native oxide overlayer developed on the grating surface.



C. SEM, AFM, **Optical microscopy**



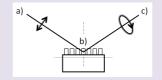
E. References

[1] M. Veis and R. Antos, J. Nanomater 2013 (2013) 621531. [2] D. C. O'Shea, T. J. Suleski, A. D. Kathman, D. W. Prather, ${\it Diffractive \ optics: design, \ fabrication, \ and \ test, \ {\it SPIE-The}}$ International Society for Optical Engineering, Bellingham, Washington (2004).

B. Spectroscopic ellipsometry

Spectroscopic ellipsometry

Principle



- a) Initial polarization state
- b) Interaction with a sample
- c) Change of the polarization

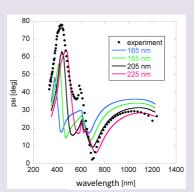
$$\frac{r_v}{r_s} = tan(\Psi)e^{i\Delta}$$

Theory

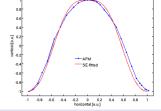
To analyse the spectro-ellipsometric experimental data, we apply rigorous coupled wave analysis (RCWA) using the correct Fourier factorization rules, which enables fast convergence. We analyze a sine-like Ni grating sample made by holographic lithography, covered by a NiO overlayer. Due to non-ideal fabrication process of both patterning and material deposition, the Ni surface relief is not perfectly sinusoidal. Therefore, for its determination we need not only the period and depth of the grooves, but also additional parameters describing their sharpness. Moreover, we also need to determine the thickness of the NiO surface overlayer.

Experimental

WVASE spectroscopic ellipsometer (Woollam, Ltd.). We have performed measurement of SE with three angles of incidence, 20, 30, and 40° in the spectral range from 300 to 1200 nm.



Results



Comparing experimental SE spectra with simulations based on various depths and profile shapes, we have found:

- (1) grating period $\Lambda = 917 \text{ nm}$,
- (2) profile depth h = 205 nm, and
- (3) the profile shape non-ideality approximated by the formula $z = (h/2)\{1 - \cos[P(y)]\}$, where P(y) = (2p/L)[Ay +(2/L)(1-A)y2] with shape profile parameter A = 0.52 (A = 0 corresponds to the ideal sinusoidal case).

Thickness of the NiO overlayer was fixed on 3.5 nm as determined by SE on non patterned part of the sample.

D. Results summary

Method	SEM	AFM	Optical microscopy	Spectroscopic ellipsometry
Grating period [nm]	916.7	917.2	918.6	917.0
Profile depth [nm]	x	170	x	205
		Real surface		Sensitive on NiO
	Fast and flexible, high	topography/	Fast and flexible	overlayer and surface
Advanteges/	resolution/ limited access	Small surface area	inspection / low	profile non-ideality,
disadvanteges	to surface profile, surface	scan, tip	resolution, no access	non-invasive/ difficult
	metallization is required	deconvolition	to depth profile	and time expensive
		artefacts		calculations

F. Conclusions

Spectroscopic ellipsometry routinely used as a characterization technique of bulk, single layers and multitayers has been proven to be also highly efficient for non-invasive characterization of laterally periodically patterned nanostructures as for example sinusoidal gratings. In this special case SE is sensitive on grating geometrical parameters (period, depth and profile shape non-ideality), material optical properties and also on presence of a surface overlayer. We have presented potentiality of SE on case study of an oxidized sinusoidal Ni grating and compared results obtained by SE with those determined by standard characterization techniques as SEM, AFM, and optical microscopy.













